Number   His   Search Text     Closes of Sept   P.N.				NB	Γime stamp
1	I Number	Hits	Search Text		
25944   sputtering and (CVD or "chemical vapor deposition")   USPAT;   US		1	("6168991").PN.		
25944   sputtering and (CVD or "chemical vapor deposition")   US-PGPUB   15:00   2002/05/02   17:39	-				
26944   2665   2676	_	638		US-PGPUB	
1789950   1789		i		USPAT;	2002/05/02
178950   178950   178950   178950   178950   178950   178950   1870	_	25944	-	00.0-	
deposition			(( -0/2) CCLS) and (sputtering and (CVD or "chemical vapor		2002/05/02
trench or hole or via or opening or recess	-	265	1 (1:11)		16:00
200		00050	an ananing or recess		
200   (((438/3), CCLS.) and (sputtering and (CVD or 'chemical vapor deposition'')) and (trench or hole or via or opening or recess) and capacitor   438/387.ccls.   13277   438/387.ccls.   13277   438/387.ccls.   13277   438/387.ccls.   13277   122   438/387.ccls.   13277   123   438/387.ccls.   13277   123   1328	-	1789950		00 - 0-	2002/05/02
deposition   ) and (trench or hole of via or Opening or via   187 ((((48/3).3CLS.) and (sputtering and (CVD or 'chemical vapor deposition')) and (trench or hole or via or opening or verses) and capacitor   USPAT;   2002/05/02   16:03   USPAT;   2002/05/02   16:03   USPAT;   2002/05/02   16:04   USPAT;   2002/05/02   US	1	200	(((438/3), CCLS.) and (sputtering and (CVD or "chemical vapor	,	
187 ((((488/3).CCLS.) and (sputtering and (CVD or "chemical vapor deposition") and recess) and capacitor	] -	200	1		
vapor deposition")) and (trench or inde of via a spanning or recess) and capacitor  488/387.ccls.  13277 ferroelectric or perovskite  12	_	187	A COLL OCT C Land (confficting and ICVI) (I Chambar		
recess.)) and capacitor 438/387.cds.  13277 ferroelectric or perovskite  13277 ferroelectric or perovskite  1328	-	/	vapor deposition"))) and (trench of flole of via of opening of	00-10102	
111   438/387.ccls.   13277			recess)) and capacitor	USPAT:	2002/05/02
13277	1 -	111	438/387.ccls.	US-PGPUB	
12   438/387.ccls. and (ferroelectric or perovskite)			1.14	USPAT;	2002/05/02
12	_	13277	ferroelectric or perovskite	US-PGPUB	
Seputtering and (CVD or "chemical vapor deposition") and (438/387,ccls. and (ferroelectric or perovskite))   USPAT;   2002/05/02   USPGPUB   USPAT;   2002/05/02   USPAT;   2002/05/0			o ( o l- and (formalectric or perovskite)		
Caputtering and (CVD or "chemical vapor deposition") and (438/387.ccls. and (ferroelectric or perovskite))   US-PGPUB   16:13   2002/05/02   438/396.ccls.   US-PGPUB   16:14   2002/05/02   USPAT;   US-PGPUB   USPAT	-	12	ł ·		
1325   1325   1325   1326   1326   1325   1325   1325   1326   1325   1325   1325   1326			(courtering and (CVD or "chemical vapor deposition")) and		
22	-	8	1 ( O /-O le and /torroblectric Or Deruyskiici)		
1325			(aputtering and (CVD or "chemical vapor deposition")) and		
1325   438/396.ccls.	-	22	428/287 cels		
Spattering and (CVD or "chemical vapor deposition") and   USPAT;   2002/05/02   16:17   237950   237		1005	438/306 ccls.		
192   192   194   194   195   195   195   196   196   196   197	-	1325		1	
192		246	(sputtering and (CVD or "chemical vapor deposition")) and		
192   193   16:16   194   195   19	-	340			2002/05/02
BLT		237950			
192		-5,70	i nr m		2002/05/02
438/396.ccls. and (terroelectric or perovskite or BST or PZT or ST or BT or BLT) (trench or hole or via or opening or recess) and (((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls. and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT)) ((trench or hole or via or opening or recess) and (((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls. and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT))) not 438/387.ccls.	_	192	((sputtering and (CVD or "chemical vapor deposition")) and	US-PGPUB	16:17
176			438/396.ccls.) and (terroelectric or perovskite of Bor of Sar		
and (CVD or "chemical vapor deposition") and 430/39/396.ccls.  172			or PZT or ST or BL1)	USPAT;	
and (ferroelectric or perovskite or BST of SBT of T2T or BLT))  ((trench or hole or via or opening or recess) and ((((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.)  and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT))) not 438/387.ccls.  1283  - 1283  (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.  (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.  (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.  (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.) (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.) (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.) (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.) (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) ush (spectrode or plate)) with sputtering usper chemical vapor deposition")  (((upper or top) with (electrode or plate)) with sputtering) (usper usper u	-	176	(trench or hole of via of opening of recess) and (((cr))	US-PGPUB	16:18
BT or BLT)   ((trench or hole or via or opening or recess) and (((sputtering and (CVD or "chemical vapor deposition")) and 438/396.ccls.)   us-PGPUB   16:57   us-PGPUB   16:57   us-PGPUB   16:57   us-PGPUB   16:57   us-PGPUB   16:58   us-PGPUB   us-PG			and (CVD or chemical vapor deposition)	:	1
((trench or hole or via or opening or recess) and (48/396.cds.) and (6VD or "chemical vapor deposition")) and 438/396.cds.  1283   438/253.cds.   USPAT; 2002/05/02   USPAT; 2002/05/02   USPGPUB   16:58   USPAT; 2002/05/02   USPGPUB   16:59   USPAT; 2002/05/02   USPGPUB   16:59   USPAT; 2002/05/02   USPGPUB   16:59   USPAT; 2002/05/02   USPGPUB   16:59   USPAT; 2002/05/02   USPGPUB   17:15   USPAT; 2002/05/02   USPGPUB   17:15   USPAT; 2002/05/02   USPGPUB   17:15   USPAT; 2002/05/02   USPGPUB   17:18   USPAT; 2002/05/02   USPGPUB   17:19   USPAT; 2002/05/02   USPGPUB   17:19   USPAT; 2002/05/02   USPGPUB   17:19   USPAT; 2002/05/02   USPGPUB   17:19   USPAT; 2002/05/03   USPA			pr pi T)		
and (CVD or "chemical vapor deposition") and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT)) not 438/387.ccls.  - 273 (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls. (trench or hole or via or opening or recess) and 438/253.ccls. (usper or top) with (electrode or plate)) with sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.) not 438/387.ccls. not 438/396.ccls. and 438/253.ccls.) not 438/387.ccls. not 438/396.ccls.  112 ((lower or bottom) with (electrode or plate)) with sputtering ((upper or top) with (electrode or plate)) with sputtering) ((lower or bottom) with (electrode or plate)) with sputtering) ((upper or top) with (electrode or plate)) with sputtering) (uspat; 2002/05/02 uspat; 2002/05/02 uspat		1570	to the learning or opening or recess) and (((Sputtering		• • • •
and (ferroelectric or perovskite of BS1 of SB1 of S	-	1/2	1 COSTD II-learning wanter denocition 11 and 4.30/.390.0000/	US-PGPUB	10.5/
BT or BLT)) not 438/387.ccls.   USPAT;   2002/05/02   USPAT;   USPAT;   2002/05/02   USPAT;   2002/05/03   U			and (ferroelectric or perovskite or BSI of SBI of TET of ST	:	•
1283   438/253.ccls.   US-PGPUB   16:58   USPAT;   2002/05/02   US-PGPUB   16:59   US-PGPUB   16:59   US-PGPUB   16:59   US-PGPUB   17:15   US-PGPUB   17:15   US-PGPUB   17:15   US-PGPUB   17:18   USPAT;   2002/05/02   US-PGPUB   17:18   US-PGPUB   17:19   US			BT or BLT))) not 438/387.ccis.	HSDAT.	2002/05/02
12		128	438/253.ccls.	US-PGPUB	
Compact of the properties of					2002/05/02
trench or hole or via or opening or recess) and 436/253.ccls capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)  (capacitor and ((sputtering and (CVD or "chemical vapor (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) deposition")) and (trench or hole or via or opening or recess) deposition")) and (trench or hole or via or opening or recess) deposition") and 438/253.ccls.) not 438/387.ccls. not 438/396.ccls.  ((lower or bottom) with (electrode or plate)) with sputtering uspart; 2002/05/02 uspart; 2002/05/03 uspart; 2	-	27:	3 (sputtering and (CVD) or "chemical vapor deposition"), and		16:58
capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)  (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) deposition")) and (trench or hole or via or opening or recess) deposition")) and (trench or hole or via or opening or recess) deposition") and (trench or hole or via or opening or recess) deposition") and (trench or hole or via or opening or recess) uspart; 2002/05/02 uspart; 2002/05/03			4. It am bala argin or opening of recess) and 4.50/200.	USPAT;	2002/05/02
and 438/253.ccls.) (capacitor and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)) not 438/387.ccls. not 438/396.ccls.  1350 ((lower or bottom) with (electrode or plate)) with sputtering ((lower or bottom) with (electrode or plate)) with (CVD or "chemical vapor deposition") (((lower or bottom) with (electrode or plate)) with sputtering) (((lower or bottom) with (electrode or plate)) with (CVD or "chemical vapor deposition")  179 (((lower or bottom) with (electrode or plate)) with (CVD or "chemical vapor deposition"))  2002/05/02 USPAT; 2002/05/03	-	26	8   capacitor and ((sputtering and (CVD))   Chemical Appl		, 16:59
Capacitor and ((sputtering and (CVD or Chemical Vapor deposition")) and (trench or hole or via or opening or recess) and 438/253.ccls.)) not 438/387.ccls. not 438/396.ccls. and 438/253.ccls.)) not 438/387.ccls. not 438/396.ccls.			1 -0/0=0 0010 1	•	1
deposition")) and (trench of fole of via to opening of via to open			1 (/taming and (CVI) or "chemical valua	USPAT;	
and 438/253.ccls.)) not 438/38/.ccls. not 436/39/section.  1350 ((lower or bottom) with (electrode or plate)) with sputtering (USPAT; US-PGPUB 17:18  ((upper or top) with (electrode or plate)) with (CVD or USPAT; US-PGPUB 17:18  "chemical vapor deposition") (((lower or bottom) with (electrode or plate)) with sputtering) uspart; USPAT; US-PGPUB 17:18  179 (((upper or top) with (electrode or plate)) with (CVD or uspart) uspart; USPAT; US-PGPUB 17:18  170 (((upper or top) with (electrode or plate)) with sputtering) uspart; USPAT; U	-	11	1 1 - 11 and (tranch of finite of Via Ut Opcilling of 100000)	US-PGPUB	17:15
- 1350 ((lower or bottom) with (electrode or plate)) with sputtering US-PGPUB 17:18  1038 ((upper or top) with (electrode or plate)) with (CVD or USPAT; 2002/05/02  "chemical vapor deposition") (((lower or bottom) with (electrode or plate)) with (CVD or and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition"))  - 50679 438/\$.ccls. USPAT; 2002/05/02  "C(((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/02  USPAT; 2002/05/02  USPAT; 2002/05/02  USPAT; 2002/05/02  USPAT; 2002/05/02  USPAT; 2002/05/03  USPAT; 2002/05/03  USPAT; 2002/05/03  USPAT; 2002/05/03  USPAT; 2002/05/03  USPAT; 17:19					0000/05/02
- 1038 ((upper or top) with (electrode or plate)) with (CVD or USPAT; 2002/05/02 US-PGPUB 17:18  - 179 (((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/02 us-PGPUB 17:18  - 50679 (((upper or top) with (electrode or plate)) with (CVD or and ((upper or top) with (electrode or plate)) with sputtering) USPAT; 2002/05/02 us-PGPUB 17:19  - 76 ((((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/03 used (((upper or top) with (electrode or plate)) with (CVD or use) use PGPUB 11:19		105	and 430/253.ccis.)) not 450/50		
- 1038 ((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition")  - 179 (((lower or bottom) with (electrode or plate)) with sputtering) and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition"))  - 50679 438/\$.ccls.  - 1038 ((upper or top) with (electrode or plate)) with sputtering) US-PGPUB 17:18  US-PGPUB 17:18  US-PGPUB 17:18  US-PGPUB 17:18  US-PGPUB 17:18  US-PGPUB 17:19  US-PGPUB 17:18	-	135			
"chemical vapor deposition") (((lower or bottom) with (electrode or plate)) with sputtering) uSPAT; 2002/05/02 uS-PGPUB 17:18  USPAT; 2002/05/02 uS-PGPUB 17:19  USPAT; 2002/05/02 "chemical vapor deposition")) uSPAT; 2002/05/02 US-PGPUB 17:19  USPAT; 2002/05/02 US-PGPUB 17:19  USPAT; 2002/05/03 US-PGPUB 17:19  USPAT; 2002/05/03 US-PGPUB 17:19 USPAT; 2002/05/03 US-PGPUB 11:19		102	((upper or top) with (electrode or plate)) with (CVD or		
- (((lower or bottom) with (electrode or plate)) with sputtering)  US-PGPUB 17:18  US-PGPUB 17:18  USPAT; 2002/05/02  US-PGPUB 17:19  USPAT; 2002/05/02  US-PGPUB 17:19  USPAT; 2002/05/03	-	103	luit luidemonition"		
and (((upper or top) with (electrode or plate)) with (electrode or plate)) with (electrode or plate)) with (electrode or plate)) with sputtering)  USPAT; 2002/05/02 US-PGPUB 17:19  ((((lower or bottom) with (electrode or plate)) with sputtering)  USPAT; 2002/05/03 USPAT; 2002/05/03 USPAT; 2002/05/03 USPAT; 11:19	-	17	with (electrode or plate)) with Sputtering)		
"chemical vapor deposition"))  USPAT; 2002/05/02 438/\$.ccls.  US-PGPUB 17:19  ((((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/03 USPAT; 2002/05/03 USPAT; 2002/05/03 USPAT; 11:19	1		and (((upper or top) with (electrode of plate)) with (exposi-	00.00	
- 50679 438/\$.ccls. US-PGPUB 17:19  ((((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/03  ord (((upper or top) with (electrode or plate)) with (CVD or US-PGPUB 11:19	1	ļ	"chemical vapor deposition"))	USPAT:	2002/05/02
- ((((lower or bottom) with (electrode or plate)) with sputtering) USPAT; 2002/05/03	-	506	79 438/\$.ccls.		17:19
76   ((((lower or bottom) with (electrode or plate)) with (CVD or US-PGPUB 11:19			(algebrade or plate)) with sputtering	) USPAT;	2002/05/03
"chemical vapor deposition"))) and 438/\$.ccls.	-		76   ((((lower or bottom) with (electrode or plate)) with (CVD or		11:19
cnemical vapor deposition /// directory			and (((upper or top) with (electrode of place))		
			cnemical vapor deposition ))) and 432/3		

			_		
[ <del>-</del>			438/240.ccls.	USPAT; US-PGPUB	2002/05/02 17:24
-			(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and	USPAT; US-PGPUB	2002/05/02 17:24
-		160	438/240.ccls. 438/244.ccls.	USPAT; US-PGPUB USPAT;	2002/05/02 17:25 2002/05/02
-		9	(sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and	US-PGPUB	17:26
-		17	438/244.ccls. ((((lower or bottom) with (electrode or plate)) with sputtering) and (((upper or top) with (electrode or plate)) with (CVD or "chemical vapor deposition"))) and ((sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or exemply or recess) and (ferroelectric or perovskite or BST or	USPAT; US-PGPUB	2002/05/02 17:26
-		316	SBT or PZT or ST or BT or BLT) and 438/240.ccls.) 204/192.17.ccls.	USPAT; US-PGPUB	2002/05/02 17:26
-		1	((((lower or bottom) with (electrode or plate)) with sputtering) and (((upper or top) with (electrode or plate)) with (CVD or	USPAT; US-PGPUB	17:27
-		4	"chemical vapor deposition"))) and 204/192.17.ccls. (sputtering and (CVD or "chemical vapor deposition")) and (trench or hole or via or opening or recess) and (ferroelectric or perovskite or BST or SBT or PZT or ST or BT or BLT) and	USPAT; US-PGPUB	2002/05/02 17:28
-		42	204/192.17.ccls. 438/for.430.ccls.	EPO; JPO; DERWENT	2002/05/02
-		3804	sputtering and (CVD or "chemical vapor deposition")	EPO; JPO; DERWENT	2002/05/02 17:29
-		0	438/for.430.ccls. and (sputtering and (CVD or "chemical vapor deposition"))	EPO; JPO; DERWENT EPO; JPO;	2002/05/02 17:29 2002/05/02
-		262545	capacitor	DERWENT	17:30
	-	32	438/for.430.ccls. and capacitor	EPO; JPO;	2002/05/02 17:30 2002/05/02
	-	57	438/for.220.ccls.	EPO; JPO; DERWENT	17:30
	-	21	capacitor and 438/for.220.ccls.	EPO; JPO; DERWENT	2002/05/02 17:31